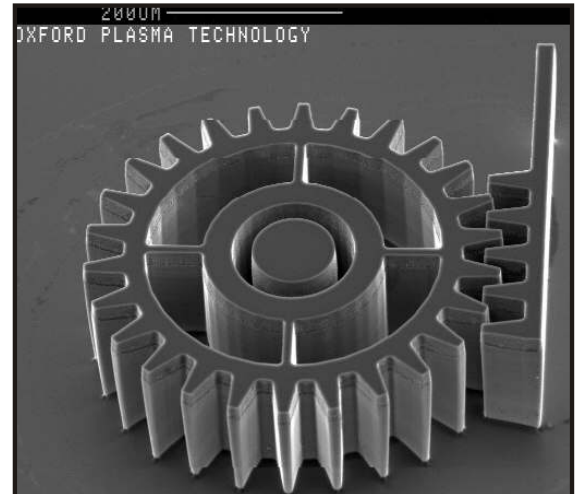
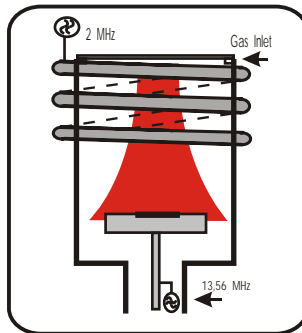
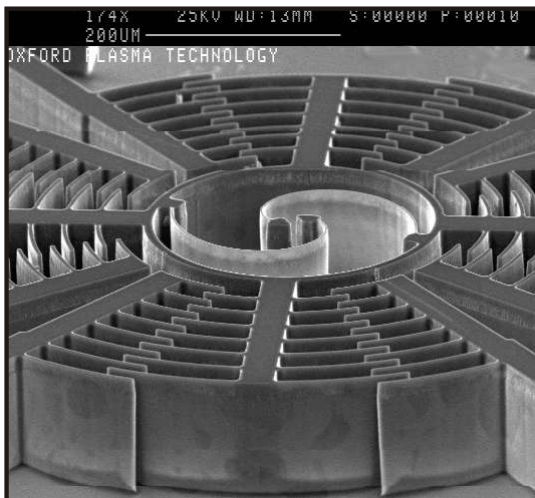
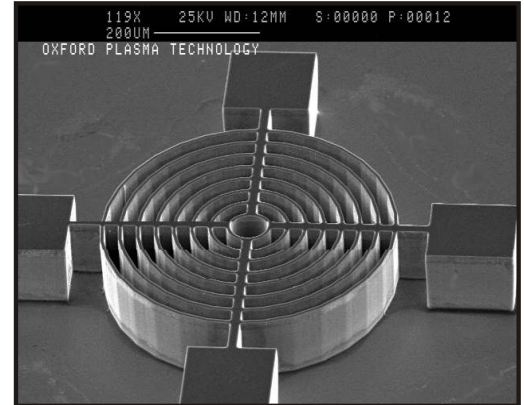
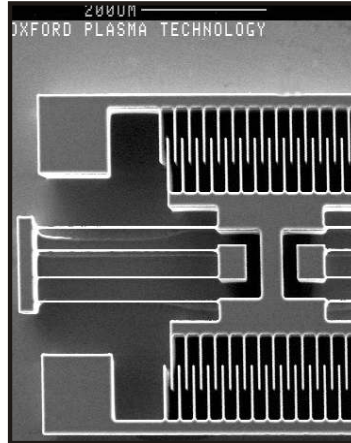
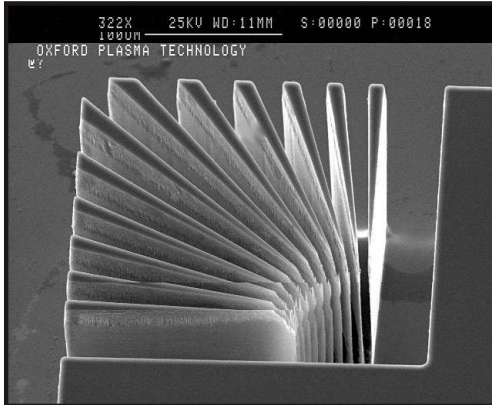


Plasmalab Data

Si etching for MEMS



etched at the OPT application lab, Yatton (UK)



Technology:

Reactive Ion Etching
Inductive Coupled Plasma Source
room temperature process
"Bosch process", gas chopping:
isotropic etch/ polymer formation
He backside cooling

Results:

Rate : up to 10 $\mu\text{m}/\text{min}$
Uniformity: $\leq \pm 2/3\%$ (4/6")
anisotropic etch
aspect ratio up to 30 : 1
controllable wall profile
high selectivity to Resist (> 75:1)
and SiO_2 (>> 100:1)

Plasmalab System 100